

RESIST PATTERN FORMING METHOD AND DEVELOPER

ABSTRACT

There are provided a method of forming a resist pattern, comprising the steps of forming a resist film containing a specific calixarene derivative on a substrate; forming a
5 pattern latent image by selectively exposing the resist film to a high-energy beam; and developing the latent image by removing parts not exposed to the high-energy beam of the resist film with a developer containing at least one
10 fluorine-containing solvent selected from the group consisting of a fluorine-containing alkyl ether and a fluorine-containing alcohol, and the fluorine-containing solvent as a resist developer.

No Suitable Figure